e-Front runners

FMP06N60ES

FUJI POWER MOSFET

Super FAP-E^{3S} series

N-CHANNEL SILICON POWER MOSFET

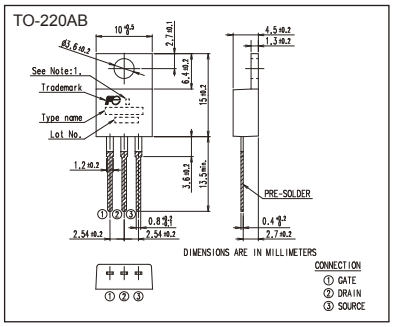
Features

Maintains both low power loss and low noise
Lower R_{DS}(on) characteristic
More controllable switching dv/dt by gate resistance
Smaller V_{GS} ringing waveform during switching
Narrow band of the gate threshold voltage (3.7±0.5V)
High avalanche durability

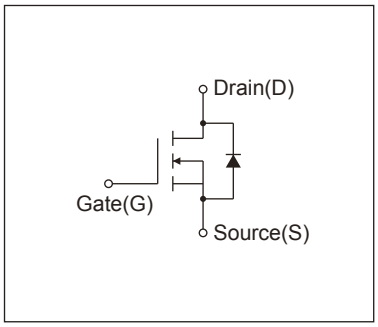
Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

Outline Drawings [mm]



Equivalent circuit schematic



Maximum Ratings and Characteristics

● Absolute Maximum Ratings at Tc=25°C (unless otherwise specified)

Description	Symbol	Characteristics	Unit	Remarks
Drain-Source Voltage	V_{DS}	600	V	
	V_{DSX}	600	V	V_{GS} = -30V
Continuous Drain Current	I_D	±6	A	
Pulsed Drain Current	I_{DP}	±24	A	
Gate-Source Voltage	V_{GS}	±30	V	
Repetitive and Non-Repetitive Maximum Avalanche Current	I_{AR}	6	A	Note*1
Non-Repetitive Maximum Avalanche Energy	E_{AS}	313.7	mJ	Note*2
Repetitive Maximum Avalanche Energy	E_{AR}	10.5	mJ	Note*3
Peak Diode Recovery dV/dt	dV/dt	3.8	kV/μs	Note*4
Peak Diode Recovery -di/dt	-di/dt	100	A/μs	Note*5
Maximum Power Dissipation	P_D	2.02	W	Ta=25°C
		105		Tc=25°C
Operating and Storage Temperature range	T_{ch}	150	°C	
	T_{stg}	-55 to + 150	°C	

● Electrical Characteristics at Tc=25°C (unless otherwise specified)

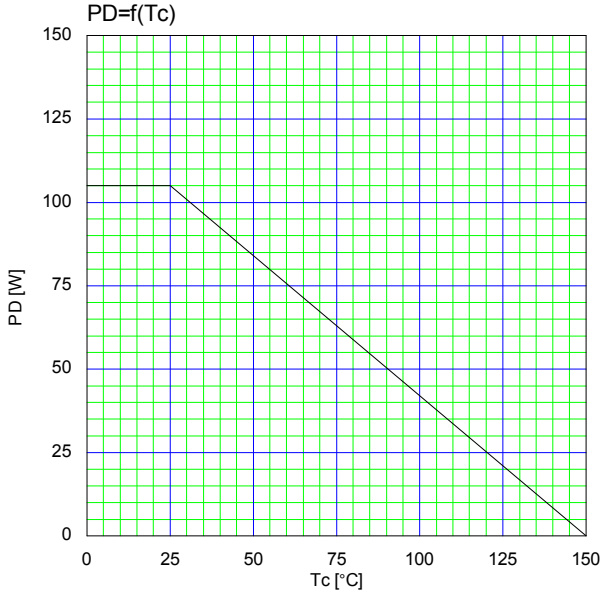
Description	Symbol	Conditions		min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250μA, V_{GS}=0V		600	-	-	V
Gate Threshold Voltage	V_{GS} (th)	I_D=250μA, V_{DS}=V_{GS}		3.2	3.7	4.2	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V, V_{GS}=0V	T_{ch}=25°C	-	-	25	μA
		V_{DS}=480V, V_{GS}=0V	T_{ch}=125°C	-	-	250	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V		-	10	100	nA
Drain-Source On-State Resistance	R_{DS} (on)	I_D=3A, V_{GS}=10V		-	1.03	1.20	Ω
Forward Transconductance	g_{fs}	I_D=3.0A, V_{DS}=25V		2.5	5	-	S
Input Capacitance	Ciss	V_{DS}=25V		-	950	1425	pF
Output Capacitance	Coss	V_{GS}=0V		-	100	150	
Reverse Transfer Capacitance	Crss	f=1MHz		-	7.5	11	
Turn-On Time	td(on)	V_{cc}=300V		-	29	43.5	ns
	tr	V_{GS}=10V		-	15	22.5	
Turn-Off Time	td(off)	I_D=3.0A		-	75	113	
	tf	R_G=27Ω		-	16	24	
Total Gate Charge	Q_G	V_{cc}=300V		-	31	46.5	nC
Gate-Source Charge	Q_{GS}	I_D=6A		-	10.5	15.8	
Gate-Drain Charge	Q_{GD}	V_{GS}=10V		-	8	12	
Gate-Drain Crossover Charge	Q_{SW}			-	4.5	6.75	
Avalanche Capability	I_{AV}	L=6.39mH, T_{ch}=25°C		6	-	-	A
Diode Forward On-Voltage	V_{SD}	I_F=6A, V_{GS}=0V, T_{ch}=25°C		-	0.90	1.35	V
Reverse Recovery Time	trr	I_F=6A, V_{GS}=0V		-	0.4	-	μs
Reverse Recovery Charge	Qrr	-di/dt=100A/μs, Tch=25°C		-	3.3	-	μC

● Thermal Characteristics

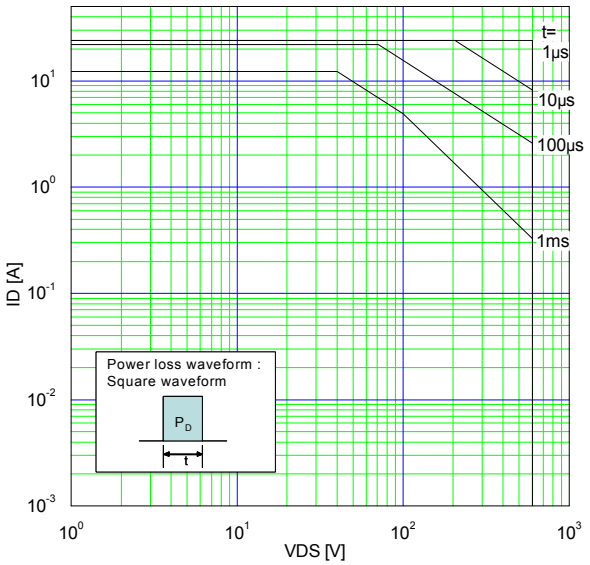
Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	Rth (ch-c)	Channel to Case			1.19	°C/W
	Rth (ch-a)	Channel to Ambient			62.0	°C/W

Note *1 : Tch≤150°C.
Note *2 : Stating Tch=25°C, I_{AS}=2.4A, L=99.8mH, Vcc=60V, R_G=50Ω.
E_{AS} limited by maximum channel temperature and avalanche current.
See to 'Avalanche Energy' graph.
Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.
See to the 'Transient Themal impeadance' graph.
Note *4 : I_F≤-I_D, -di/dt=100A/μs, Vcc≤BV_{DSS}, Tch≤150°C.
Note *5 : I_F≤-I_D, dv/dt=3.8kV/μs, Vcc≤BV_{DSS}, Tch≤150°C.

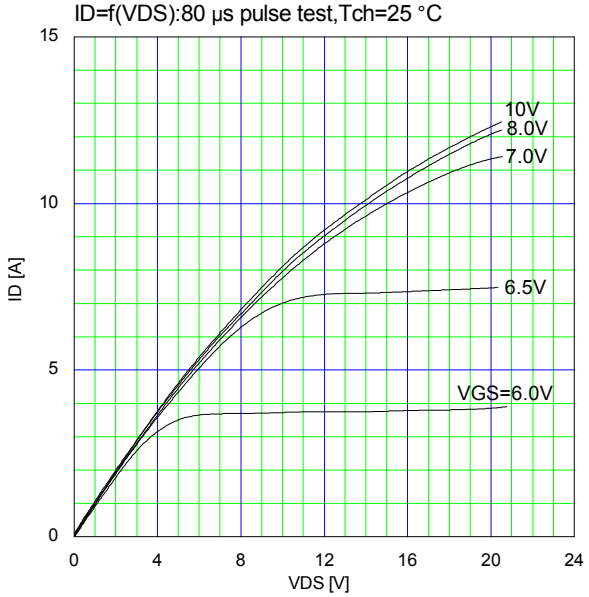
Allowable Power Dissipation
PD=f(Tc)



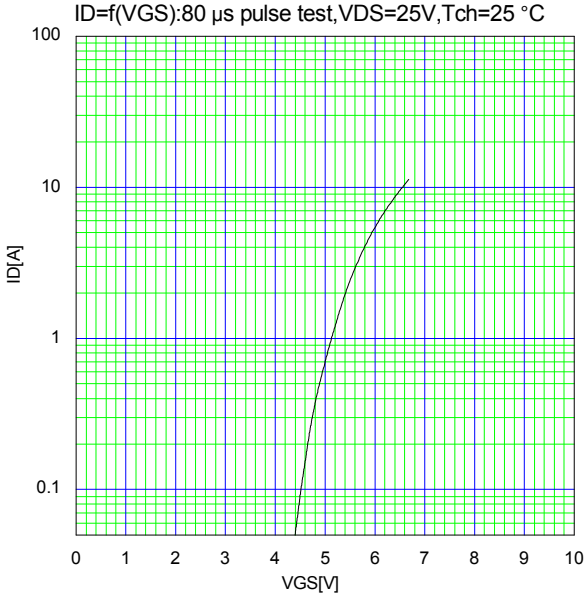
Safe Operating Area
I_D=f(V_{DS}):Duty=0(Single pulse),Tc=25 °c



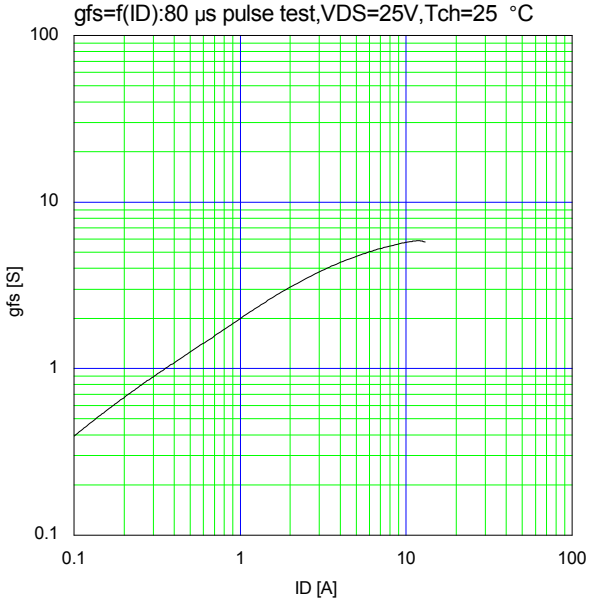
Typical Output Characteristics
ID=f(VDS):80 µs pulse test,Tch=25 °C



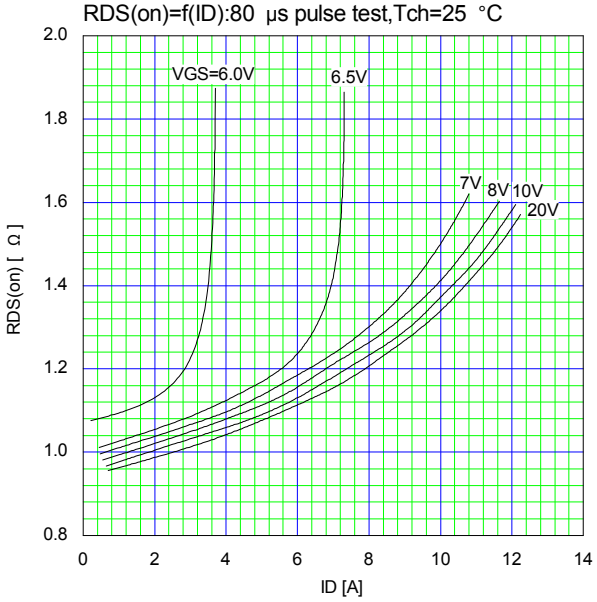
Typical Transfer Characteristic
ID=f(VGS):80 µs pulse test,VDS=25V,Tch=25 °C



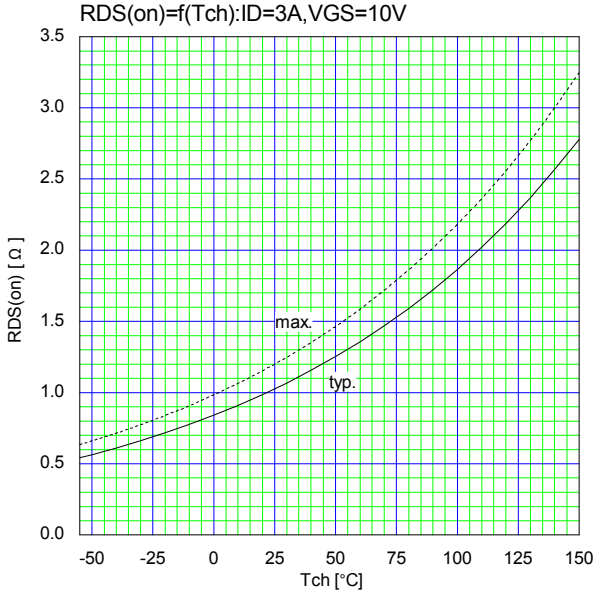
Typical Transconductance
gfs=f(ID):80 µs pulse test,VDS=25V,Tch=25 °C



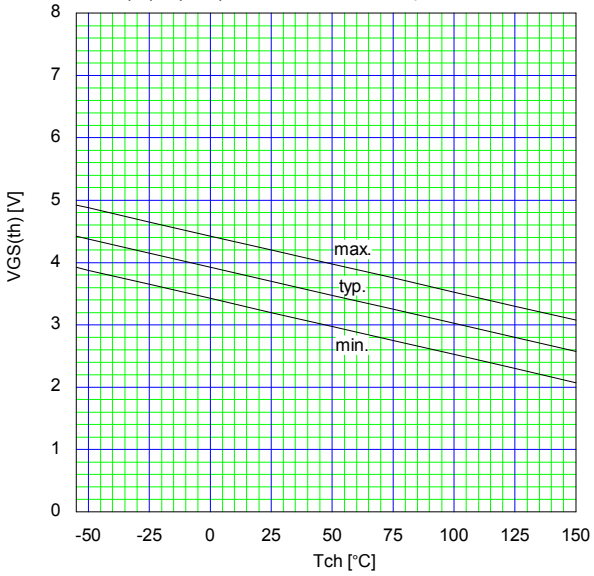
Typical Drain-Source on-state Resistance
RDS(on)=f(ID):80 µs pulse test,Tch=25 °C



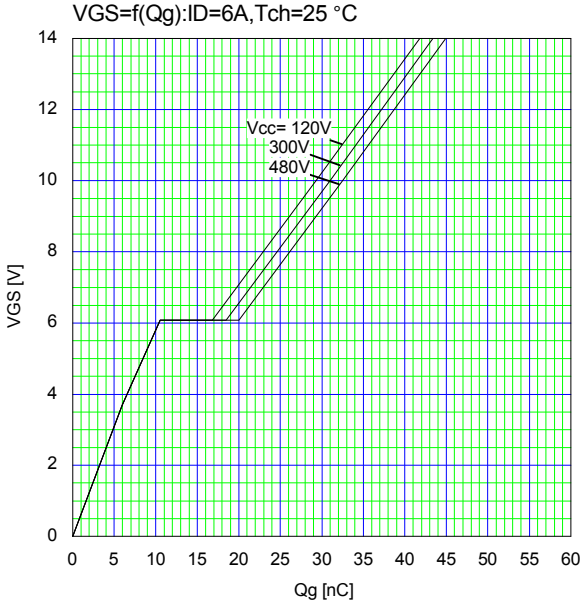
Drain-Source On-state Resistance
RDS(on)=f(Tch):ID=3A,VGS=10V



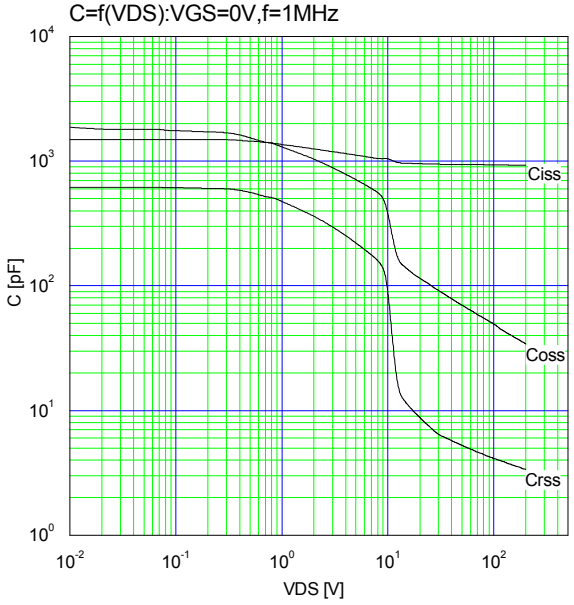
Gate Threshold Voltage vs. Tch
VGS(th)=f(Tch):VDS=VGS,ID=250μA



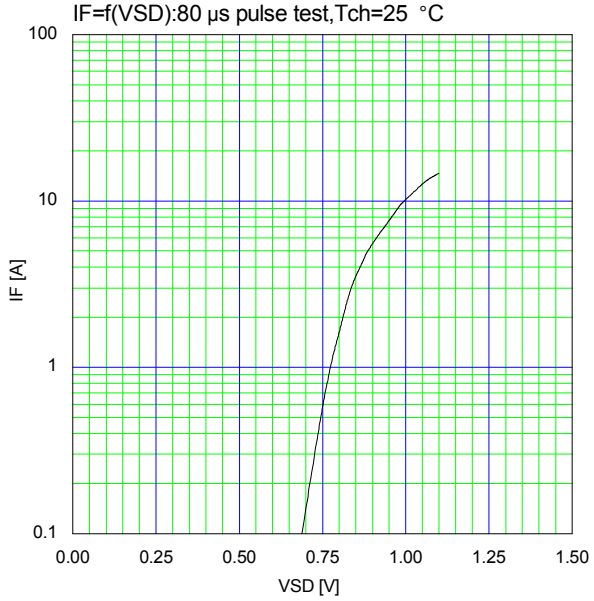
Typical Gate Charge Characteristics
VGS=f(Qg):ID=6A,Tch=25 °C



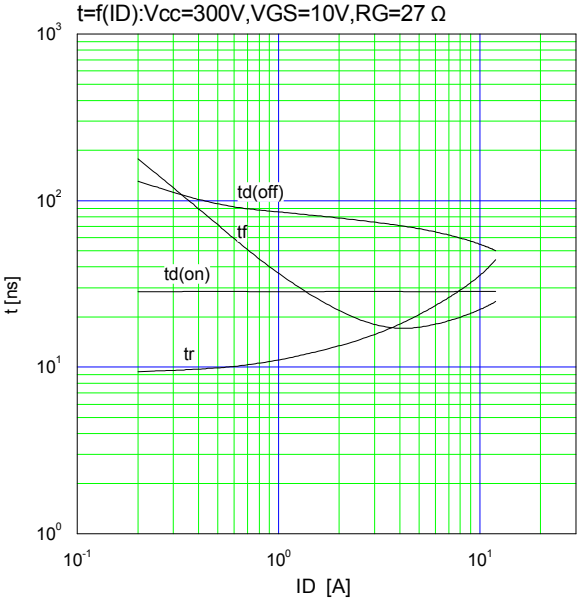
Typical Capacitance
C=f(VDS):VGS=0V,f=1MHz



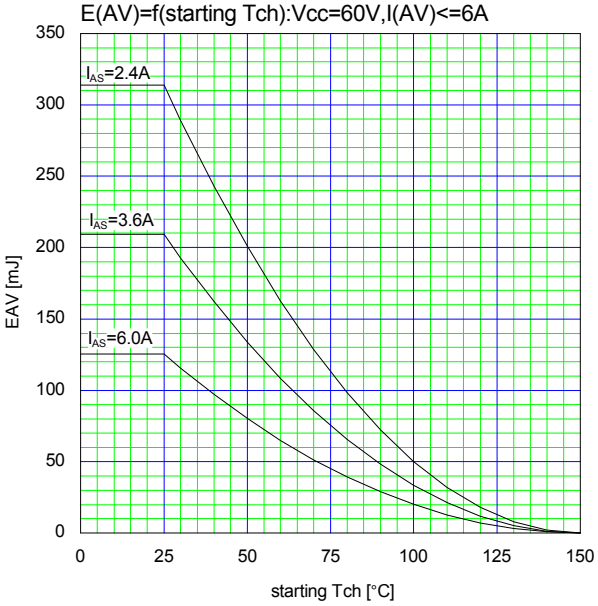
Typical Forward Characteristics of Reverse Diode
IF=f(VSD):80 μs pulse test,Tch=25 °C



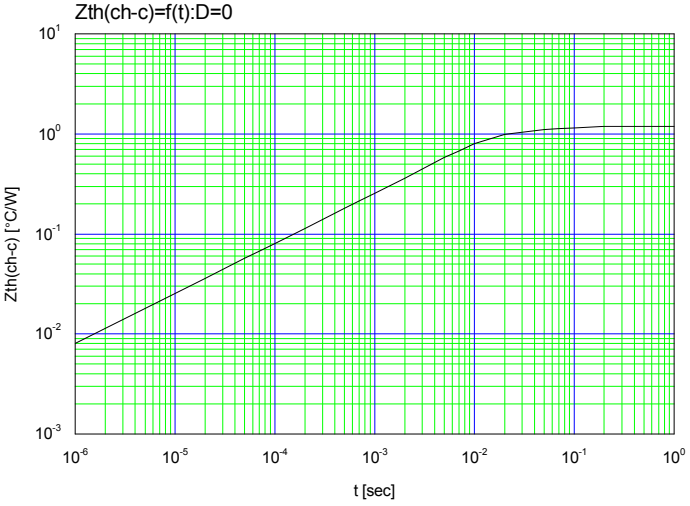
Typical Switching Characteristics vs. ID
t=f(ID):Vcc=300V,VGS=10V,RG=27 Ω



Maximum Avalanche Energy vs. starting Tch
E(AV)=f(starting Tch):Vcc=60V,I(AV)<=6A



Maximum Transient Thermal Impedance
Zth(ch-c)=f(t):D=0



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